

U231, U232, U233, U234, U235

N-Channel Matched Dual Silicon Junction Field-Effect Transistor

- Differential Amplifier
- Low & Maximum Frequency Amplifier

Absolute maximum ratings at $T_A = 25^\circ\text{C}$

Reverse Gate Source & Gate Drain Voltage	-50V
Continuous Forward Gate Current	50 mA
Continuous Device Power Dissipation	300 mW
Power Derating	4.3 mW/ $^\circ\text{C}$
Operating Temperature Range	-55 $^\circ\text{C}$ to +125 $^\circ\text{C}$
Storage Temperature Range	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$

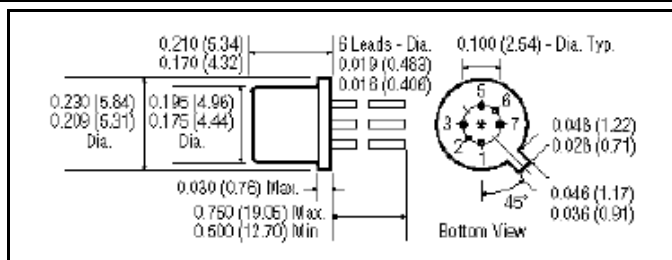
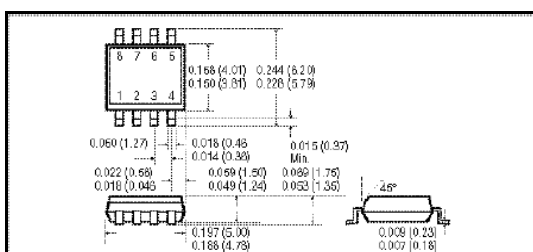
At 25 $^\circ\text{C}$ free air temperature Static Electrical Characteristics

		U231, U232, U233, U234, U235				Process NJ16	
		Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	-50			V	$I_G = -1 \mu\text{A}$, $V_{DS} = 0 \text{ V}$	
Gate Reverse Current	I_{GSS}			-100 -500	pA nA	$V_{GS} = -30 \text{ V}$, $V_{DS} = 0 \text{ V}$	150 $^\circ\text{C}$
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	-0.5		-4.5	V	$V_{DS} = 20 \text{ V}$, $I_D = 1 \text{ nA}$	
Gate Source On Voltage	V_{GS}	-0.3		-4	V	$V_{DG} = 20 \text{ V}$, $I_D = 200 \mu\text{A}$	
Drain Saturation Current (pulsed)	I_{DSS}	0.5		5	mA	$V_{DS} = 20 \text{ V}$, $V_{GS} = 0 \text{ V}$	
Gate Current	I_G			-50 -250	pA nA	$V_{DG} = 20 \text{ V}$, $I_D = 200 \mu\text{A}$	125 $^\circ\text{C}$

Dynamic Electrical Characteristics

Common-Source Forward Transconductance	g_{fs}	0.6		1.6	mS	$V_{DG} = 20 \text{ V}$, $I_D = 200 \mu\text{A}$	1 kHz
Common-Source Output Transconductance	g_{os}			10	μS	$V_{DG} = 20 \text{ V}$, $I_D = 200 \mu\text{A}$	1 kHz
Common-Source Input Capacitance	C_{iss}			6	pF	$V_{DS} = 20 \text{ V}$, $V_{GS} = 0 \text{ V}$	1 MHz
Common-Source Reverse Transfer Capacitance	C_{rss}			2	pF	$V_{DS} = 20 \text{ V}$, $V_{GS} = 0 \text{ V}$	1 MHz
Equivalent Short Circuit Input Noise Voltage	$\sim e_N$			80	nV/ $\sqrt{\text{Hz}}$	$V_{DS} = 20 \text{ V}$, $V_{GS} = 0 \text{ V}$	100 Hz

Matching Characteristics		U231	U232	U233	U234	U235	Units	Test Conditions
Differential Gate-Source Voltage	$ V_{GS1} - V_{GS2} $	5	10	15	20	25	mV	$V_{DG} = 20 \text{ V}$, $I_D = 200 \mu\text{A}$
Differential Gate Source Voltage w/ Temperature (-55 $^\circ\text{C}$, 25 $^\circ\text{C}$, 125 $^\circ\text{C}$)	$\frac{\Delta V_{GS1} - V_{GS2} }{\Delta T}$	10	25	50	75	100	$\mu\text{V}/^\circ\text{C}$	$V_{DG} = 20 \text{ V}$, $I_D = 200 \mu\text{A}$



SOIC-8 Package Pin Configuration
 SMPU231, SMPU232, 1-G1, 2-D1, 3-S1, 4-G2,
 SMPU233, SMPU234 5-G2, 6-D2, 7-S2, 8-G1
 SMPU235

TO-71: Pin Configuration
 U231, U232, U233, 1-S1, 2-D1, 3-G1,
 U234, U235 4-S2, 5-D2, 6-G2
 Dimensions in Inches (mm)



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